Microelectronic Circuits Assignment 1

Set 1

Sai Kartik (2020A3PS0435P) Manpreet Singh (2020A3PS0419P) Rajeev Rajagopal (2020A3PS1237P)

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1 Question 1

Value of components (resistor/capacitor) present in the circuit:

Table 1: Calculated values for question 1

Sl. No.	Component Name	Value
1	$R1(k\Omega)$	$15k\Omega$
2	C1 (nF)	1nF

1.1 Circuit as on LT SPICE

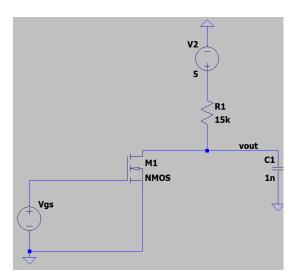


Figure 1: Circuit for question 1

1.2 Graphs

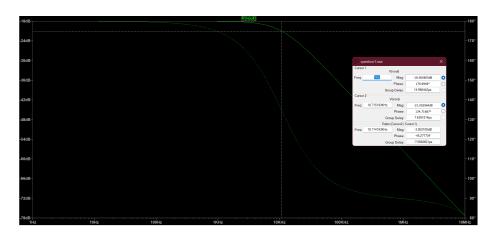


Figure 2: Frequency Response

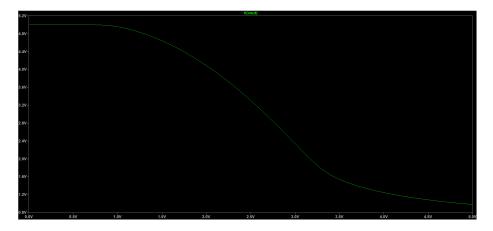


Figure 3: Voltage transfer characteristics

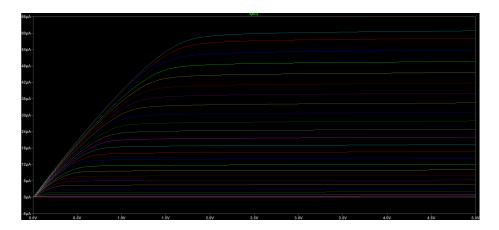


Figure 4: Graph of i_{DS} vs V_{DS}

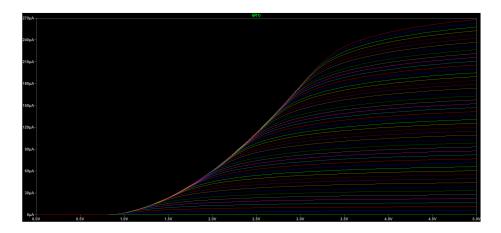


Figure 5: Graph of i_{DS} vs V_{GS}

In figure 2 on the preceding page, for an approximate 3dB change in frequency (as shown by both cursors), we see the phase shift by approximately 45° .

1.3 Miscellaneous calculations

1.3.1 DC operating point

Given the overdrive voltage of the MOSFET as 0.2V and the threshold voltage as 0.6696061V, to calculate the DC operating point, we must take $V_{GS} = V_{TH} + V_{OV} = 0.8696061$ V. With this value of V_{GS} , the simulation yields the following values:

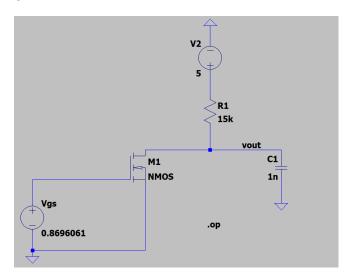


Figure 6: DC operating point circuit

```
--- Operating Point ---
V(n002):
                 0.869606
                                voltage
V(n001):
                                voltage
V(vout):
                 4.99329
                                voltage
Id (M1) :
                 4.47302e-007
                               device_current
Ig(M1):
Ib(M1):
                                device_current
                 -5.00329e-012 device_current
Is(M1):
                 -4.47297e-007 device_current
I (C1):
                 -4.99329e-021 device_current
                 4.47302e-007 device_current
I(R1):
                 -4.47302e-007 device_current
0 device_current
I(V2):
I (Vgs) :
```

Figure 7: DC operating point parameters

1.3.2 Small signal calculations

Transconductance g_m is given by:

$$g_m = \frac{2I_D}{V_{OV}}$$

Using the values found above from the DC operating point calculations, we can calculate the transconductance to be

$$g_m = \frac{2 \times 4.47302 \times 10^{-7}}{0.2} = 4.47302 \times 10^{-6} A/V$$

The value of the output resistance r_0 corresponding to the early effect/channel length modulation is given by:

$$r_0 = \left(\frac{\partial i_D}{\partial V_{DS}}\right)^{-1} \bigg|_{V_{GS} = \text{constant}}$$

This can be found out from the simulation by setting $V_{GS} = V_{TH} + V_{OV}$ and finding the value of the inverse of the differential at $V_{DS} = 5$ V.

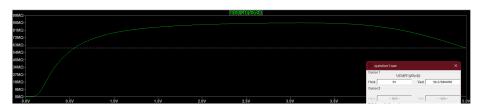


Figure 8: Output resistance for small signal calculations

The value of r_0 we get from this graph is $r_0 = 59.272865 \text{M}\Omega$. Collectively, we get the small signal model as below:

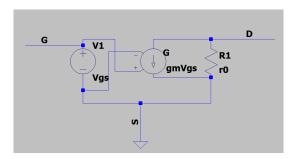


Figure 9: Small signal model

2 Question 2

Value of components (resistors/gain) present in the circuit

Table 2: Calculated values for question 2

		1
Sl. No.	Component Name	Value
1	$R_1(k\Omega)$	$30 \mathrm{k}\Omega$
2	$R_2(k\Omega)$	$17 \mathrm{k}\Omega$
3	$R_3(k\Omega)$	$30 \mathrm{k}\Omega$
4	$R_4(k\Omega)$	$50 \mathrm{k}\Omega$
5	k	18 V/V

2.1 Circuit as on LT SPICE

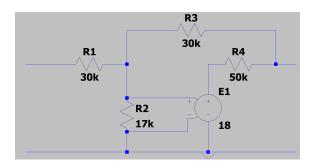


Figure 10: Original 2 port network simulated on LT SPICE

2.2 Z, Y and H Parameters

2.2.1 Z parameters

Z parameters as obtained from LT SPICE

$$Z = \begin{bmatrix} 23.492822k\Omega & -4.0669856k\Omega \\ -47.99043k\Omega & -11.24402k\Omega \end{bmatrix}$$

2.2.2 Y parameters

Y parameters as obtained from LT SPICE

$$Y = \begin{bmatrix} 24.479166\mu \mho & -8.8541665\mu \mho \\ -104.47916\mu \mho & -51.145835\mu \mho \end{bmatrix}$$

2.2.3 H parameters

$$H = \begin{bmatrix} 40.851062k\Omega & 361.70211m\text{V/V} \\ -4.268085\text{A/A} & -88.936169\mho \end{bmatrix}$$

2.3 Calculations

2.3.1 Z parameters

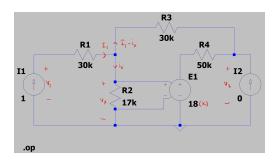


Figure 11: Z parameter circuit 1 (for z_{11} and z_{21})

Assume the convention in the above circuit for the calculations that follow

$$-(I_{1} - i_{x})(R_{3} + R_{4}) - kV_{x} + V_{x} = 0$$

$$(i_{x} - I_{1})(R_{3} + R_{4}) = V_{x}(k - 1)$$

$$(i_{x} - I_{1})(R_{3} + R_{4}) = i_{x}R_{2}(k - 1)$$

$$i_{x}(R_{3} + R_{4} - R_{2}(k - 1)) = I_{1}(R_{3} + R_{4})$$

$$\implies i_{x} = I_{1} \frac{(R_{3} + R_{4})}{R_{3} + R_{4} - R_{2}(k - 1)}$$

$$V_{1} = I_{1}R_{1} + V_{x}$$

$$V_{1} = I_{1}R_{1} + i_{x}R_{2}$$

$$V_{1} = I_{1} \left[R_{1} + \frac{R_{2}(R_{3} + R_{4})}{R_{3} + R_{4} - R_{2}(k - 1)} \right]$$

$$\implies \frac{V_{1}}{I_{1}} = \begin{bmatrix} z_{11} = R_{1} + \frac{R_{2}(R_{3} + R_{4})}{R_{3} + R_{4} - R_{2}(k - 1)} \end{bmatrix}$$

$$Also:$$

$$V_{2} = (I_{1} - i_{x})R_{4} + kV_{x}$$

$$V_{2} = (I_{1} - i_{x})R_{4} + ki_{x}R_{2}$$

$$V_{2} = i_{x}(kR_{2} - R_{4}) + I_{1}R_{4}$$

$$V_{2} = I_{1} \left[R_{4} + \frac{(kR_{2} - R_{4})(R_{3} + R_{4})}{R_{3} + R_{4} + R_{2}(k - 1)} \right]$$

$$\implies \frac{V_{2}}{I_{1}} = \begin{bmatrix} z_{21} = R_{4} + \frac{(kR_{2} - R_{4})(R_{3} + R_{4})}{R_{3} + R_{4} - R_{2}(k - 1)} \end{bmatrix}$$

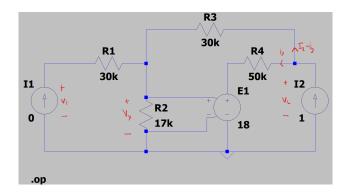


Figure 12: Z parameter circuit 2 (for z_{12} and z_{22})

Assume the convention in the above circuit for the calculations that follow

$$-R_{3}(I_{2} - i_{y}) - V_{x} + kV_{x} + i_{y}R_{4} = 0$$

$$i_{y}R_{4} - R_{3}(I_{2} - i_{y}) = (1 - k)V_{x}$$

$$i_{y}R_{4} - R_{3}(I_{2} - i_{y}) = (1 - k)(I_{2} - i_{y})R_{2}$$

$$i_{y}R_{4} = (I_{2} - i_{y})[(1 - k)R_{2} + R_{3}]$$

$$(R_{4} + R_{3} + (1 - k)R_{2})i_{y} = I_{2}[(1 - k)R_{2} + R_{3}]$$

$$\implies i_{y} = I_{2} \frac{(1 - k)R_{2} + R_{3}}{(1 - k)R_{2} + R_{3} + R_{4}}$$

$$V_{2} = i_{y}R_{4} + kV_{x}$$

$$V_{2} = i_{y}R_{4} + k(I_{2} - i_{y})R_{2}$$

$$V_{2} = i_{y}[R_{4} - kR_{2}] + KI_{2}R_{2}$$

$$V_{2} = I_{2} \left[\frac{(R_{4} - kR_{2})\{(1 - k)R_{2} + R_{3}\}}{(1 - k)R_{2} + R_{3} + R_{4}} + kR_{2} \right]$$

$$\implies \frac{V_{2}}{I_{2}} = \left[z_{22} = \frac{(R_{4} - kR_{2})\{(1 - k)R_{2} + R_{3}\}}{(1 - k)R_{2} + R_{3} + R_{4}} + kR_{2} \right]$$

$$Also:$$

$$V_{1} = V_{x} = (I_{2} - i_{y})R_{2}$$

$$V_{1} = I_{2}R_{2} \left[1 - \frac{(1 - k)R_{2} + R_{3}}{(1 - k)R_{2} + R_{3} + R_{4}} \right]$$

$$\implies \frac{V_{1}}{I_{2}} = \left[z_{12} = R_{2} \left[1 - \frac{(1 - k)R_{2} + R_{3}}{(1 - k)R_{2} + R_{3} + R_{4}} \right]$$

Using the corresponding values taken from table 2 on page 6 into the above equations, we get the matrix for the Z parameters:

$$Z = \begin{bmatrix} 23.49282297k\Omega & -4.066985646k\Omega \\ -47.99043062k\Omega & -11.244041914k\Omega \end{bmatrix}$$

Which is in accordance with the values obtained from the simulation.

2.3.2 Y parameters

From the above matrix for Z parameters, we can calculate the Y parameters as follows:

$$\Delta Z = z_{11}z_{22} - z_{12}z_{21}$$

$$\implies \Delta Z = [(23.49282297 \times -11.244041914) - (-47.99043062 \times -4.066985646)] \times 10^{3}$$

$$\Delta Z = -459.326 \times 10^{6}$$

$$Y = \begin{bmatrix} \frac{z_{22}}{\Delta Z} & -\frac{z_{12}}{\Delta Z} \\ -\frac{z_{21}}{\Delta Z} & \frac{z_{11}}{\Delta Z} \end{bmatrix}$$

Simplifying the above matrix, we get the Y parameters:

$$Y = \begin{bmatrix} 2.448 \times 10^{-5} \mu \mho & -8.8541 \times 10^{-6} \mu \mho \\ -1.104480 \times 10^{-4} \mu \mho & -5.11 \times 10^{-5} \mu \mho \end{bmatrix}$$

2.3.3 H parameters

Similarly, we can calculate the H parameters as follows:

$$H = egin{bmatrix} rac{\Delta Z}{z_{22}} & -rac{z_{12}}{z_{22}} \ -rac{z_{21}}{z_{22}} & rac{1}{z_{22}} \end{bmatrix}$$

Simplifying the above matrix, we get the H parameters:

$$H = \begin{bmatrix} 40.8507k\Omega & -0.3617\text{V/V} \\ -4.2681\text{A/A} & -88.9363\mho \end{bmatrix}$$

2.4 Load resistance value at port 2

Varying the output resistance at the terminals of port 2 and by calculating the voltage and current across the resistance, we can calculate the maximum power dissipated across the resistance. This can be seen in the following figure:

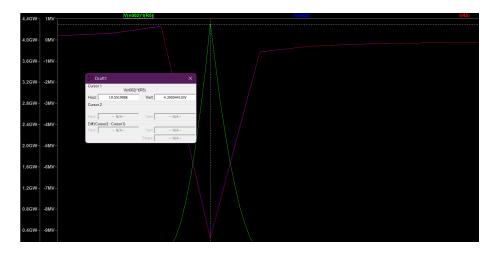


Figure 13: Load resistance value at port 2

According to the simulation results shown above, the value for the resistance at which maximum power transfer occurs is $19.551998k\Omega$ and the maximum power transferred is 4.3005441GW. The circuit used to determine the above graph is shown below:

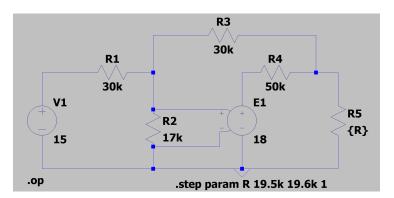


Figure 14: Circuit used to calculate the maximum power transfer point

The values through which the resistance is varied, is deduced through trial and error to get a clear graph.